Abstracts

A bias dependent HEMT noise model

L. Klapproth, A. Schaefer and G. Boeck. "A bias dependent HEMT noise model." 1997 MTT-S International Microwave Symposium Digest 2. (1997 Vol. II [MWSYM]): 881-884.

We present a model to describe the noise performance of HEMTs in dependence of the applied gate and drain voltages. The model is based on two uncorrelated noise sources at the intrinsic transistor. Temperatures related to resistors in the intrinsic transistor model are used to model the noise behavior of the device. By using the correlation matrix technique the parameters are extracted from noise parameter measurements in a straightforward manner.

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